

HAF1002(L), HAF1002(S)

Silicon P Channel MOS FET Series Power Switching

REJ03G1133-0200
(Previous: ADE-208-586)
Rev.2.00
Sep 07, 2005

Description

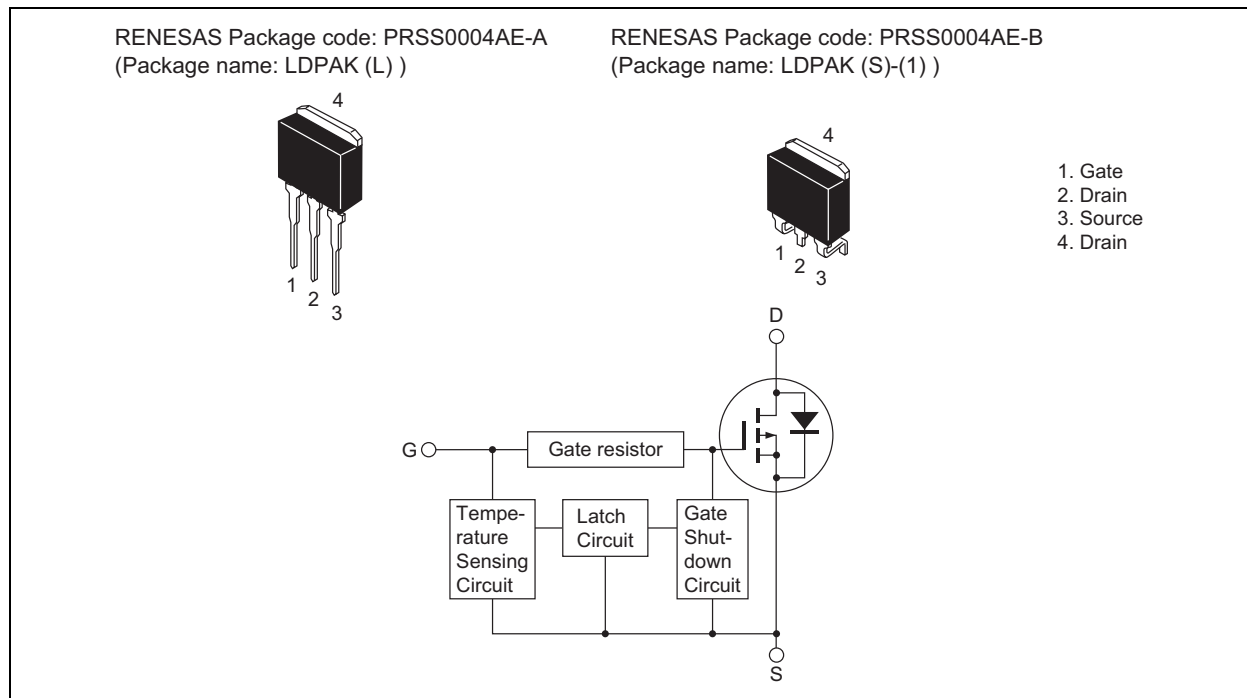
This FET has the over temperature shut-down capability sensing to the junction temperature.

This FET has the built-in over temperature shut-down circuit in the gate area. And this circuit operation to shut-down the gate voltage in case of high junction temperature like applying over power consumption, over current etc.

Features

- Logic level operation (−4 to −6 V Gate drive)
- High endurance capability against to the short circuit
- Built-in the over temperature shut-down circuit
- Latch type shut-down operation (Need 0 voltage recovery)

Outline



Absolute Maximum Ratings

(T_a = 25°C)

Item	Symbol	Value	Unit
Drain to source voltage	V _{DSS}	-60	V
Gate to source voltage	V _{GSS}	-16	V
	V _{GSS}	3	V
Drain current	I _D	-15	A
Drain peak current	I _{D (pulse)} ^{Note 1}	-30	A
Body-drain diode reverse drain current	I _{DR}	-15	A
Channel dissipation	P _{ch} ^{Note 2}	50	W
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1%

2. Value at T_c = 25°C

Typical Operation Characteristics

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Input voltage	V _{IH}	-3.5	—	—	V	
	V _{IL}	—	—	-1.2	V	
Input current (Gate non shut down)	I _{IH1}	—	—	-100	μA	V _i = -8 V, V _{DS} = 0
	I _{IH2}	—	—	-50	μA	V _i = -3.5 V, V _{DS} = 0
	I _{IL}	—	—	-1	μA	V _i = -1.2 V, V _{DS} = 0
Input current (Gate shut down)	I _{IH (sd) 1}	—	-0.8	—	mA	V _i = -8 V, V _{DS} = 0
	I _{IH (sd) 2}	—	-0.35	—	mA	V _i = -3.5 V, V _{DS} = 0
Shut down temperature	T _{sd}	—	175	—	°C	Channel temperature
Gate operation voltage	V _{OP}	-3.5	—	-13	V	

Electrical Characteristics

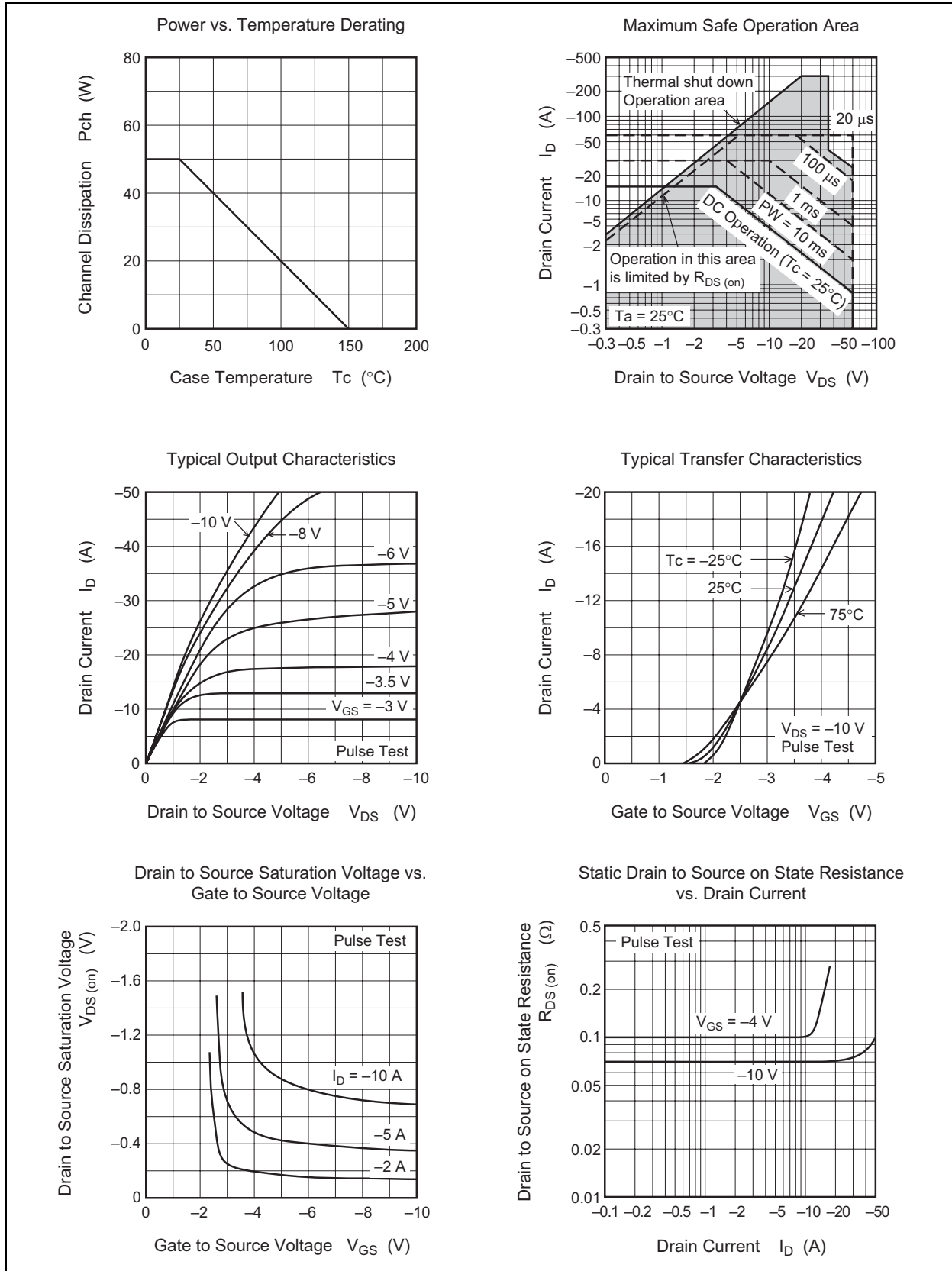
(T_a = 25°C)

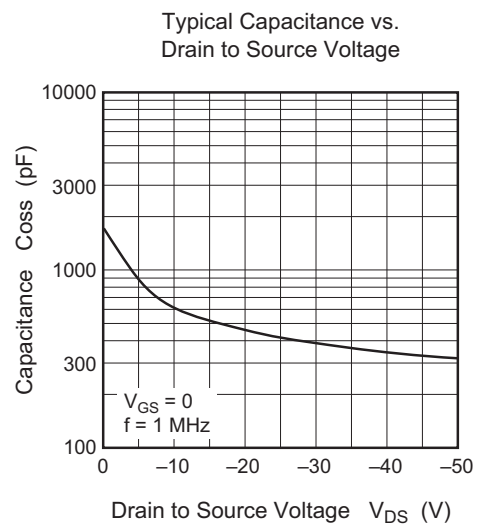
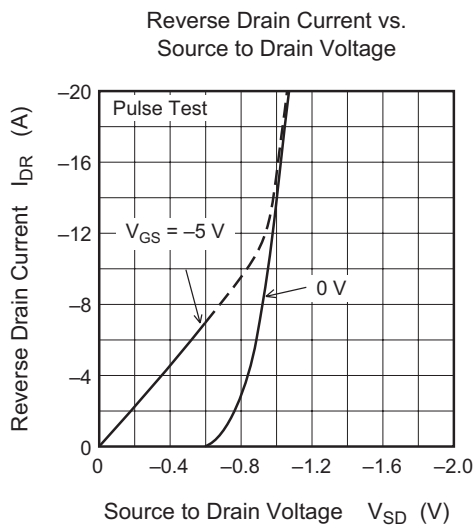
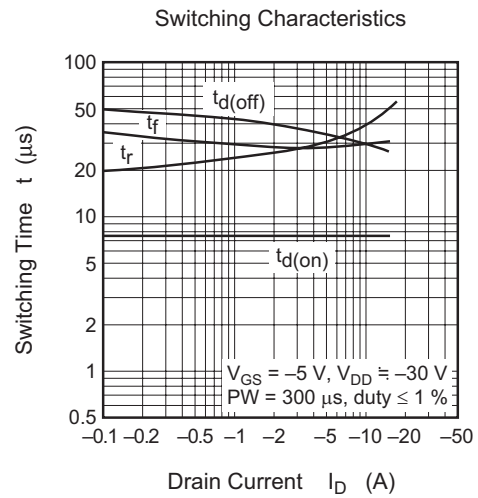
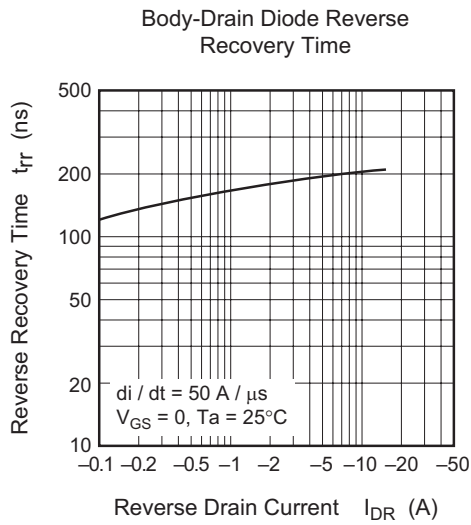
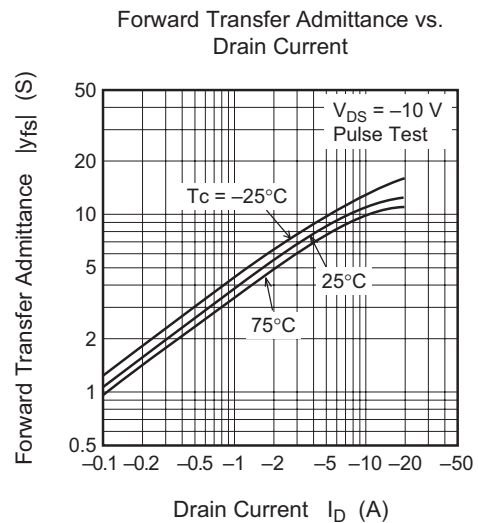
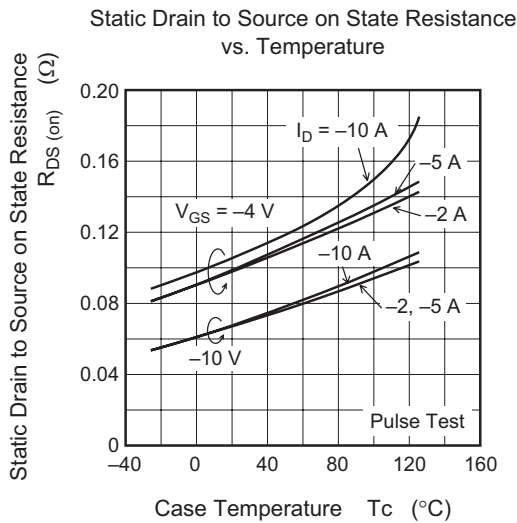
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain current	I _{D1}	-7	—	—	A	V _{GS} = -3.5 V, V _{DS} = -2 V
	I _{D2}	—	—	-10	mA	V _{GS} = -1.2 V, V _{DS} = -2 V
Drain to source breakdown voltage	V _{(BR) DSS}	-60	—	—	V	I _D = -10 mA, V _{GS} = 0
Gate to source breakdown voltage	V _{(BR) GSS}	-16	—	—	V	I _G = -100 μA, V _{DS} = 0
	V _{(BR) GSS}	3	—	—	V	I _G = 100 μA, V _{DS} = 0
Gate to source leak current	I _{GSS1}	—	—	-100	μA	V _{GS} = -8 V, V _{DS} = 0
	I _{GSS2}	—	—	-50	μA	V _{GS} = -3.5 V, V _{DS} = 0
	I _{GSS3}	—	—	-1	μA	V _{GS} = -1.2 V, V _{DS} = 0
	I _{GSS4}	—	—	100	μA	V _{GS} = 2.4 V, V _{DS} = 0
Input current (shut down)	I _{GS (op) 1}	—	-0.8	—	mA	V _{GS} = -8 V, V _{DS} = 0
	I _{GS (op) 2}	—	-0.35	—	mA	V _{GS} = -3.5 V, V _{DS} = 0
Zero gate voltage drain current	I _{DSS}	—	—	-250	μA	V _{DS} = -50 V, V _{GS} = 0
Gate to source cutoff voltage	V _{GS (off)}	-1.1	—	-2.25	V	I _D = -1 mA, V _{DS} = -10 V
Static drain to source on state resistance	R _{DS (on)}	—	100	130	mΩ	I _D = -7.5 A, V _{GS} = -4 V ^{Note 3}
	R _{DS (on)}	—	70	90	mΩ	I _D = -7.5 A, V _{GS} = -10 V ^{Note 3}
Forward transfer admittance	y _{fs}	5	10	—	S	I _D = -7.5 A, V _{DS} = -10 V ^{Note 3}
Output capacitance	C _{oss}	—	610	—	pF	V _{DS} = -10 V, V _{GS} = 0 f = 1 MHz
Turn-on delay time	t _{d (on)}	—	7.5	—	μs	I _D = -7.5 A V _{GS} = -5 V R _L = 4 Ω
Rise time	t _r	—	36	—	μs	
Turn-off delay time	t _{d (off)}	—	32	—	μs	
Fall time	t _f	—	29	—	μs	
Body-drain diode forward voltage	V _{DF}	—	-1.0	—	V	I _F = -15 A, V _{GS} = 0
Body-drain diode reverse recovery time	t _{rr}	—	200	—	ns	I _F = -15 A, V _{GS} = 0 di _F /dt = 50 A/μs
Over load shut down operation time ^{Note4}	t _{os1}	—	3.7	—	ms	V _{GS} = -5 V, V _{DD} = -12 V
	t _{os2}	—	1	—	ms	V _{GS} = -5 V, V _{DD} = -24 V

Notes: 3. Pulse test

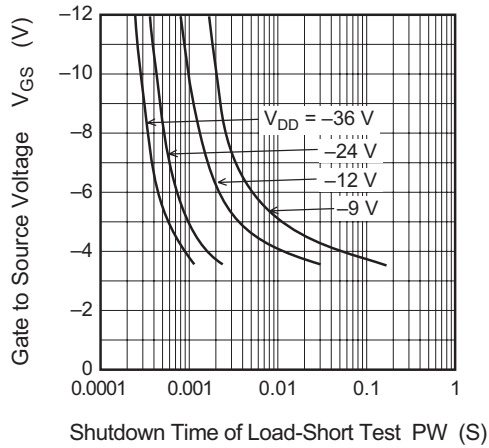
4. Include the time shift based on increasing of channel temperature when operate under over load condition.

Main Characteristics

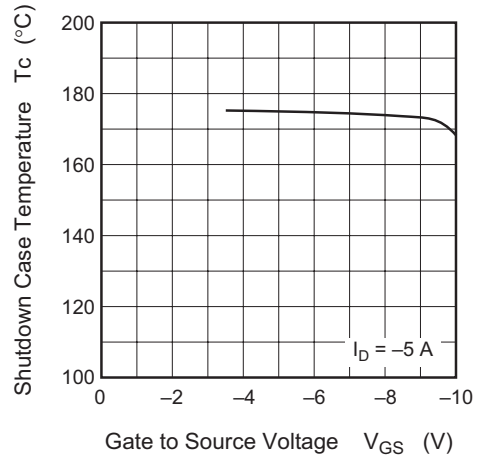




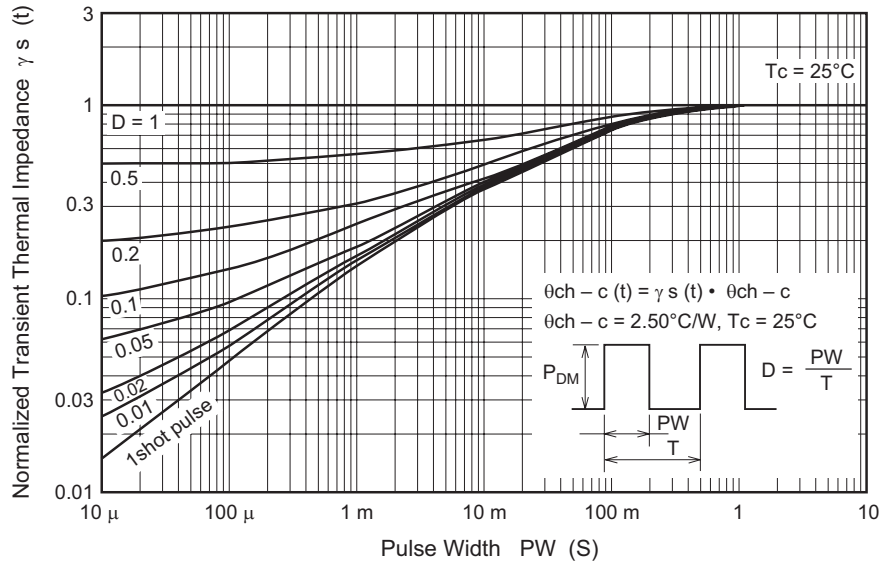
Gate to Source Voltage vs. Shutdown Time of Load-Short Test



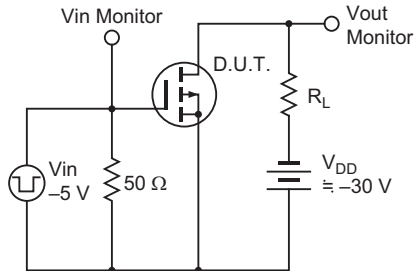
Shutdown Case Temperature vs. Gate to Source Voltage



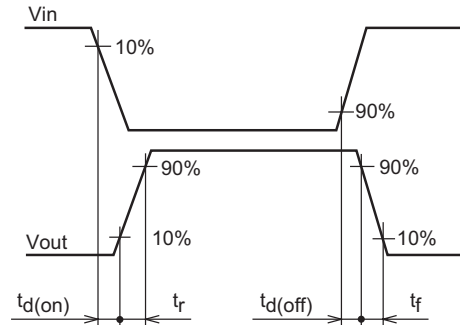
Normalized Transient Thermal Impedance vs. Pulse Width



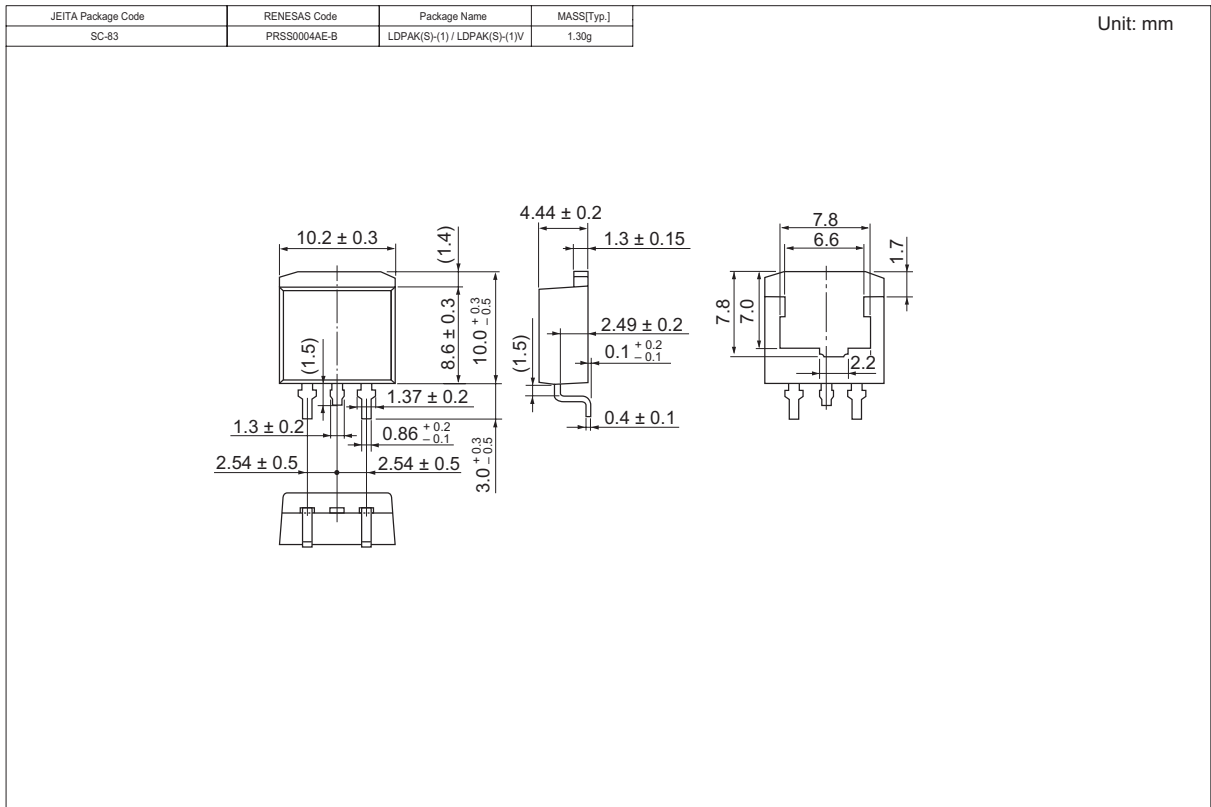
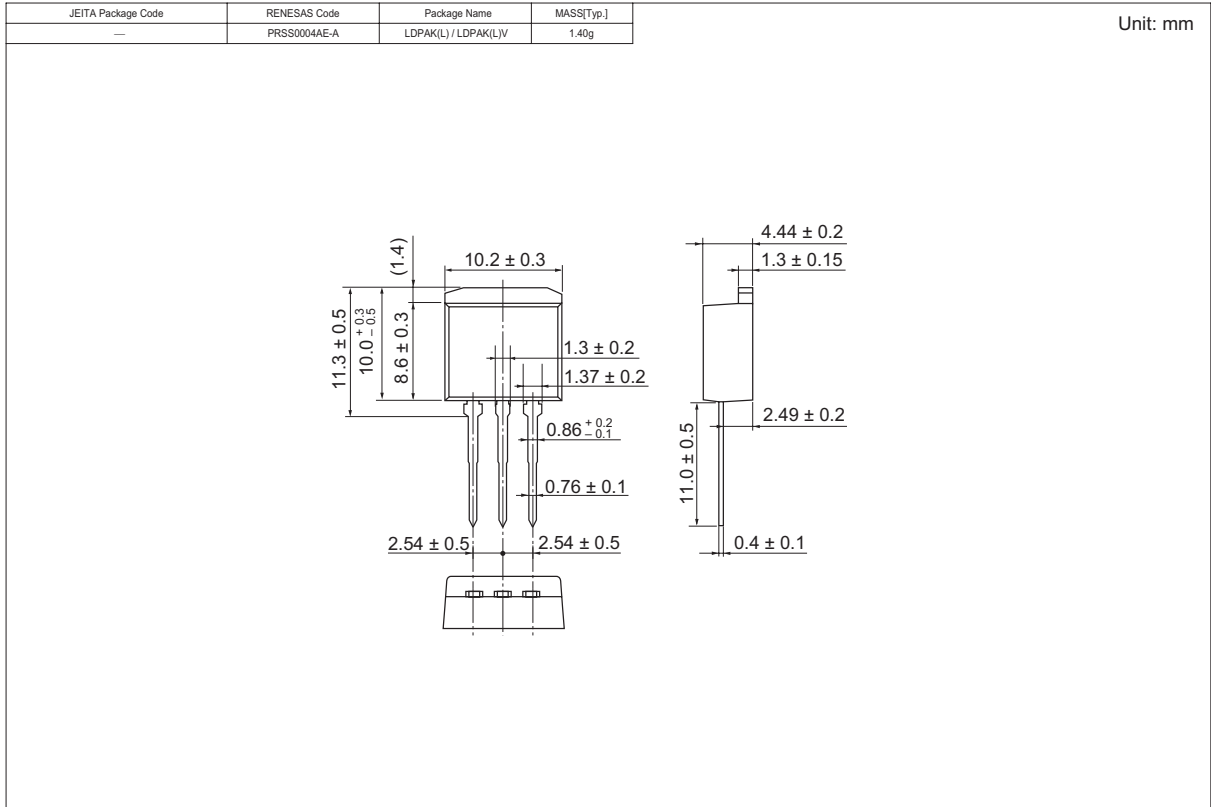
Switching Time Test Circuit



Waveform



Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
HAF1002-90L	Max: 50 pcs/sack	Sack
HAF1002-90S	Max: 50 pcs/sack	Sack
HAF1002-90STL	1000 pcs/Reel	Embossed tape
HAF1002-90STR	1000 pcs/Reel	Embossed tape

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